

BUK7K45-100E

Dual N-channel 100 V, 37.6 mΩ standard level MOSFET

2 September 2015

Product data sheet

1. General description

Dual Standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- · Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------------------------|--------------------------------------|---|--|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 100 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 21.4 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | - | 53 | W |
| Static characte | Static characteristics FET1 and FET2 | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$ | | - | 30 | 37.6 | mΩ |
| Dynamic characteristics FET1 and FET2 | | | | | | | |
| Q_{GD} | gate-drain charge | $I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$ | | - | 9.7 | - | nC |



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|---|----------------|
| 1 | S1 | source1 | 8 7 6 5 | D1 D1 D2 D2 |
| 2 | G1 | gate1 | \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\ | |
| 3 | S2 | source2 | | |
| 4 | G2 | gate2 | | |
| 5 | D2 | drain2 | | |
| 6 | D2 | drain2 | | mbk725 |
| 7 | D1 | drain1 | 1 2 3 4 LFPAK56D (SOT1205) | |
| 8 | D1 | drain1 | (0011200) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|--------------|----------|--|---------|--|--|
| | Name | Description | Version | | |
| BUK7K45-100E | LFPAK56D | Plastic single ended surface mounted package (LFPAK56D); 8 leads | SOT1205 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|--------------|--------------|
| BUK7K45-100E | 74510E |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|---|-----|------|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 100 | V |
| V_{DGR} | drain-gate voltage | R_{GS} = 20 k Ω | - | 100 | V |
| V _{GS} | gate-source voltage | T _j ≤ 175 °C; DC | -20 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | 53 | W |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u> | - | 21.4 | Α |
| | | T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u> | - | 15 | Α |
| I _{DM} | peak drain current | T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3 | - | 84 | Α |

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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|---|--------|-----|------|------|
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| T _j | junction temperature | | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | | - | 260 | °C |
| Source-drai | n diode FET1 and FET2 | | | | | |
| I _S | source current | T _{mb} = 25 °C | | - | 21.4 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 84 | Α |
| Avalanche I | Ruggedness FET1 and FET2 | | | | ' | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 21.4 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4 | [1][2] | - | 46 | mJ |

- [1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

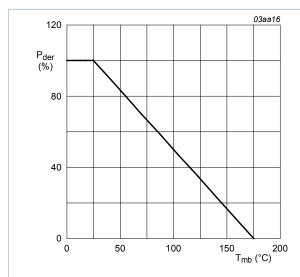


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

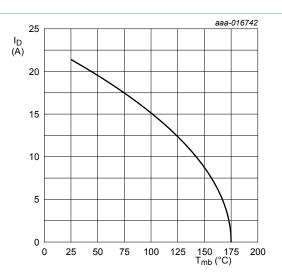


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10V$$

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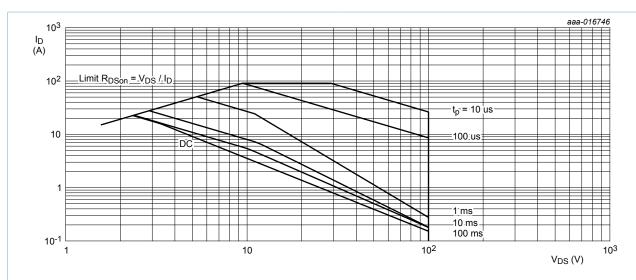


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



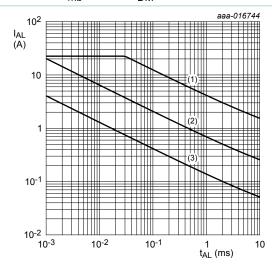


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1)
$$T_{j(init)} = 25$$
°C; (2) $T_{j(init)} = 150$ °C; (3) Repetitive Avalanche

9. Thermal characteristics

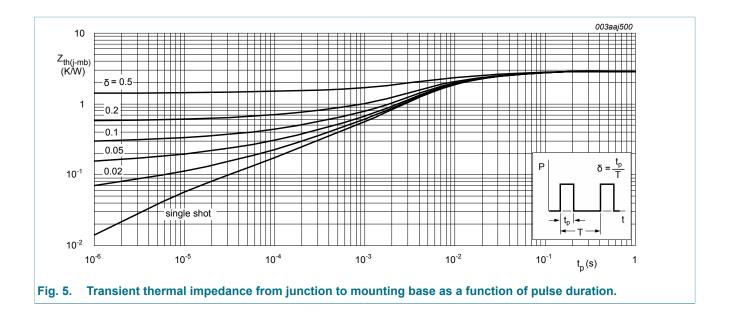
Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|---|-----|-----|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 5 | - | - | 2.84 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | Minimum footprint; mounted on a printed circuit board | - | 95 | - | K/W |

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------------------------|---|---|-----|------|------|------|
| Static char | acteristics FET1 and FET2 | | , | | | _ |
| V _{(BR)DSS} drain-source | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$ | 90 | - | - | V | |
| | breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$ | 100 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 9; Fig. 10 | 2.4 | 3 | 4 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10 | 1 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10 | - | - | 4.5 | V |
| I _{DSS} drain leakage | drain leakage current | V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C | - | 0.02 | 1 | μA |
| | | V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C | - | - | 500 | μΑ |
| I _{GSS} gate leakage current | gate leakage current | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| | | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state | $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 11$ | - | 30 | 37.6 | mΩ |
| | resistance | V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 11; Fig. 12 | - | 80 | 104 | mΩ |
| Dynamic cl | haracteristics FET1 and FE | ET2 | | | ' | |
| Q _{G(tot)} | total gate charge | I _D = 5 A; V _{DS} = 80 V; V _{GS} = 10 V; | - | 25.9 | - | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u> | - | 4.3 | - | nC |
| Q_{GD} | gate-drain charge | | - | 9.7 | - | nC |

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--------------------|------------------------------|---|--|-----|------|------|------|
| C _{iss} | input capacitance | $V_{GS} = 0 \text{ V; } V_{DS} = 25 \text{ V; } f = 1 \text{ MHz;}$ $T_j = 25 \text{ °C; } Fig. 15$ | | - | 1150 | 1533 | pF |
| C _{oss} | output capacitance | | | - | 122 | 147 | pF |
| C _{rss} | reverse transfer capacitance | | | - | 84 | 115 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 80 V; R_{L} = 16 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C | | - | 6.2 | - | ns |
| t _r | rise time | | | - | 11.2 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | | - | 20.3 | - | ns |
| t _f | fall time | V_{DS} = 80 V; R_{L} = 16 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C | | - | 13.9 | - | ns |
| Source-dra | ain diode FET1 and FET2 | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$ | | - | 0.78 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ | | - | 32.9 | - | ns |
| Q _r | recovered charge | $V_{DS} = 50 \text{ V}; T_j = 25 \text{ °C}$ | | - | 44 | - | nC |

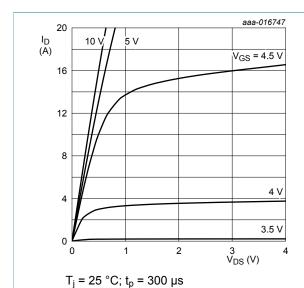


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

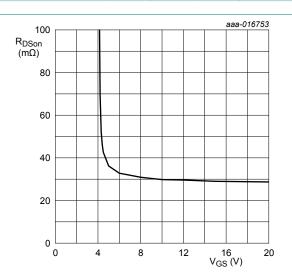


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values $T_j = 25^{\circ}C, \ I_D = 5A$

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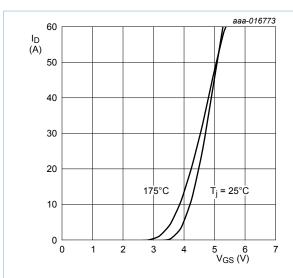


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



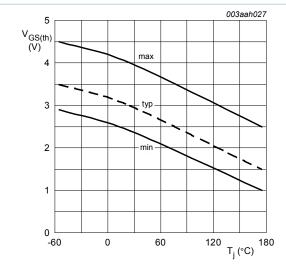


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA; V_{DS} = V_{GS}

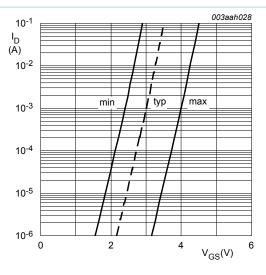
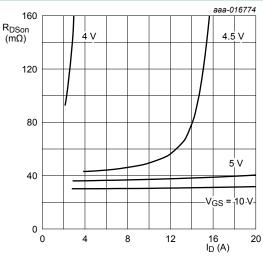


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C; $V_{DS} = 5V$



 $T_i = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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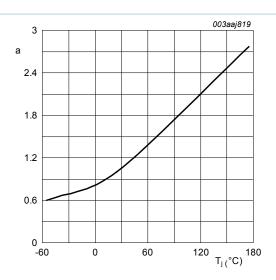


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}C)}$$

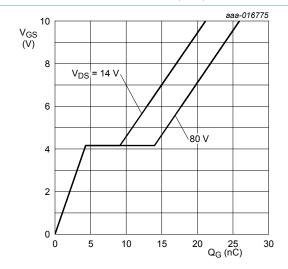


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_i = 25^{\circ}C; I_D = 5A$$

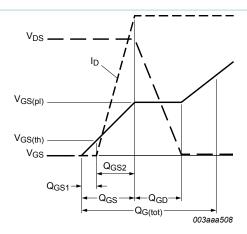


Fig. 13. Gate charge waveform definitions

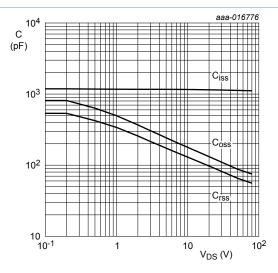


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V$$
; $f = 1MHz$

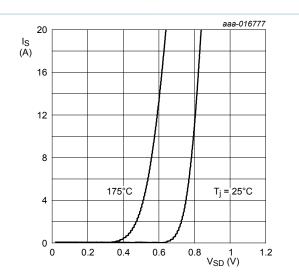


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values $V_{\rm GS} = 0V$

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11. Package outline

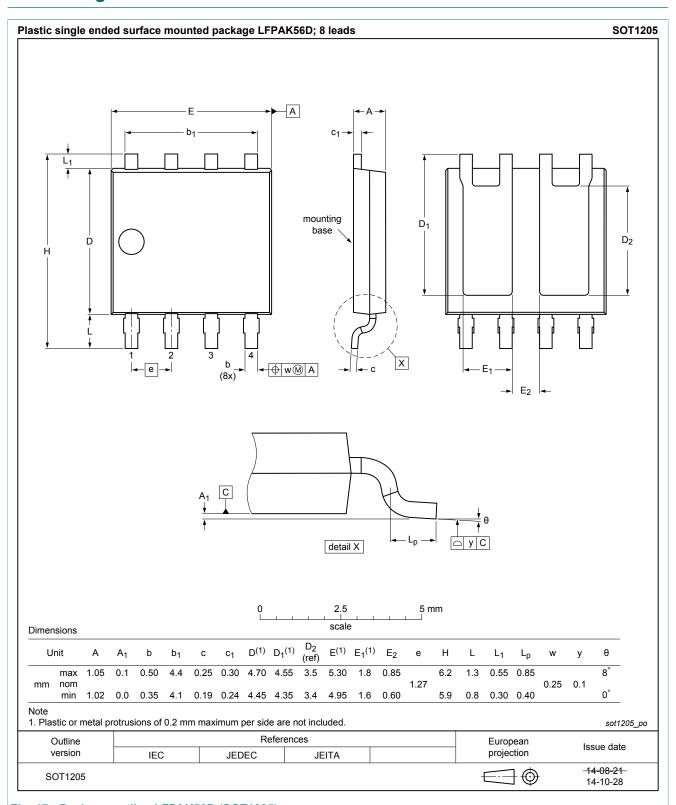


Fig. 17. Package outline LFPAK56D (SOT1205)

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12. Legal information

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|--------------------------------------|--------------------|---|
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